Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of the claims in the applications.

Listing of Claims:

1. (Currently amended) A method for actively adjusting the back bias voltage of one or more CMOS transistors comprising the steps:

fabricating a reference transistor on a chip,

monitoring the leakage current of the reference transistor with an active dc output control circuit without using a clock signal, and

adjusting the back bias voltage of the well containing the reference transistor until the leakage current is below a preset value.

2. (Original) The method of claim 1 wherein said reference transistor comprises a P-MOS transistor in a P-MOS well or a N-MOS transistor in a N-MOS well.

3. (Original) The method of claim 1 wherein said monitoring and said adjusting are performed by an active dc output control circuit not on the same chip as the reference transistor.

4. (Original) The method of claim 1 wherein said active dc output control circuit monitors and adjusts at least one P-MOS well and at least one N-MOS well.

5. (Original) The method of claim 1 wherein there is one or more active dc output control circuits on the same chip with one or more said reference transistors.

6. (Original) The method of claim 1wherein said preset leakage value is determined by the mask design of said active dc output control circuit.

7. (Original) The method of claim 1wherein said preset leakage valuc is stored in programmable circuit elements of said active dc output control circuit after fabrication.

8. (Original) The method of claim 7 wherein said preset leakage value is stored in re-programmable circuit elements of said active dc output control circuit after fabrication.

9. (Original) The method of claim 8 wherein said active dc output control circuit processes a signal to set said preset leakage value in said reprogrammable circuit elements of said active dc output control circuit.

10. (Original) The method of claim 9 wherein said active dc output control contains re-programmable circuit elements and addressing means for one or more preset leakage values.

11. (Currently amended) An integrated circuit for actively adjusting the back bias voltage of one or more CMOS transistors comprising:

a means for monitoring the leakage current of a reference transistor on a chip without using a clock signal,

a means for adjusting the back bias voltage of the well containing the reference transistor,

a means for determining when the leakage current is below a preset value, and

a means for maintaining the back bias voltage and the leakage current in a narrow range.

12. (Original) The integrated circuit of claim 11 wherein said integrated circuit is not on the same chip as the reference transistor.

13. (Original) The integrated circuit of claim 11 wherein said reference transistor comprises a P-MOS transistor in a P-MOS well or a N-MOS transistor in a N-MOS well.

14. (Original) The integrated circuit of claim 11 wherein said leakage current preset values are stored in programmable memory.

15. (Original) The integrated circuit of claim 11 further comprising a means to adjust the back bias of a well not containing the reference transistor.

16. (Currently amended) An integrated circuit for actively adjusting one or more ~~of its~~ output voltages based on monitoring the current of one or more CMOS transistors comprising:

a means for monitoring the current of one or more CMOS transistors without using a clock signal,

a means for adjusting one or more ~~of its~~ output voltages,

a means for determining when the monitored one or more currents is below a preset value,

a means for maintaining ~~its~~ one or more output voltages in a narrow range, and

a means for storing the preset values in programmable memory.

17. (Currently amended) An integrated circuit for actively adjusting the threshold voltage of one or more CMOS transistors comprising:

a means for monitoring the leakage current of a reference transistor on a chip without using a clock signal;

a means for adjusting the back bias voltage of the well containing the reference transistor;

a means for determining when the leakage current is about a proset value;

a means for maintaining the back bias voltage and the leakage in a narrow range; and

a means for correlating said leakage current with the threshold voltage.